

Octal Bus Buffer

MC74VHC244, MC74VHCT244A

The MC74VHC244/MC74VHCT244A is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology.

The device is a noninverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The MC74VHC244 inputs are compatible with standard CMOS levels while the MC74VHCT244A inputs are compatible with TTL levels. The MC74VHCT244A device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The MC74VHC244 and MC74VHCT244A inputs tolerate voltages up to 5.5 V, allowing the interface of 5 V systems to 3 V systems.

The MC74VHCT244A output structures provide protection when $V_{\rm CC}$ = 0 V. These output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

• High Speed: $t_{PD} = 3.8 \text{ ns (Typ)}$ at VCC = 5.0 V (VHC)

 t_{PD} = 5.6 ns (Typ) at VCC = 5.0 V (VHCT)

- Low Power Dissipation: $I_{CC} = 4.0 \,\mu\text{A}$ (Max) at $T_A = 25^{\circ}\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\%$
- Power Down Protection Provided
- Balanced Propagation Delays
- Designed for: 2.0 V to 5.5 V (VHC)

4.5 V to 5.5 V (VHCT)

• Low Noise: $V_{OLP} = 0.8 \text{ V (Max) (VHC)}$

 $V_{OLP} = 1.1 \text{ V (Max) (VHCT)}$

- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance: Human Body Model > 2000 V;
- Chip Complexity: 136 FETs
- –Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

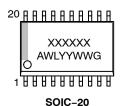


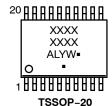
SOIC-20 DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E

MARKING DIAGRAMS



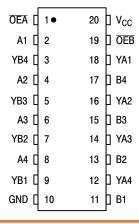


3010-20

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

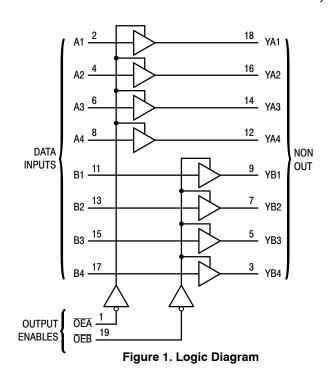
PIN ASSIGNMENT



ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

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FUNCTION TABLE

INP	UTS	OUTPUTS			
OEA, OEB	A, B	YA, YB			
L	L	L			
L	Н	Н			
Н	X	Z			

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V
V _{IN}	DC Input Voltage	-0.5 to +6.5	V
V _{OUT}	DC Output Voltage (MC74VHC)	-0.5 to V _{CC} +0.5	V
	DC Output Voltage (MC74VHCT) Active Mode (High or Low State) Tristate Mode (Note 1) Power-Off Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +6.5 -0.5 to +6.5	
I _{IN}	DC Input Current, per Pin	±20	mA
I _{OUT}	DC Output Current, Per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
I _{IK}	Input Clamp Current	-20	mA
I _{OK}	Output Clamp Current MC74VHC244 MC74VHCT244A	±20 –20	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs	260	°C
TJ	Junction Temperature Under Bias	+150	°C
$ heta_{\sf JA}$	Thermal Resistance (Note 2) SOIC-20W TSSOP-20	96 150	°C/W
P_{D}	Power Dissipation in Still Air at 25°C SOIC–20W TSSOP–20	1302 833	mW
MSL	Moisture Sensitivity	Level 1	_
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.244 in	_
V _{ESD}	ESD Withstand Voltage (Note 3) Human Body Model Charged Device Model	2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.

2. Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.

3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A.

⁽Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	P	arameter	Min	Max	Unit
MC74VHC				•	
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 5)		0	V _{CC}	V
T _A	Operating Temperature		-55	+125	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V
MC74VHC	Т			•	
V _{CC}	DC Supply Voltage		4.5	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 5)	Active Mode (High or Low State) Tristate Mode Power-Off Mode ($V_{\rm CC}$ = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature		-55	+125	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 4.5 V to 5.5 V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

5. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

DC CHARACTERISTICS (MC74VHC244)

			Vcc	1	Γ _A = 25°	С	T _A ≤	85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.5 V _{CC} x 0.7			1.5 V _{CC} x 0.7		1.5 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.5 V _{CC} x 0.3		0.5 V _{CC} x 0.3		0.5 V _{CC} x 0.3	V
V _{OH}	Maximum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		٧
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	٧
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = 4$ mA $I_{OH} = 8$ mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
l _{OZ}	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current (per package)	V _{IN} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHC244)

				T _A = 25°	С	T _A ≤	85°C		C ≤ T _A 25°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.8 8.3	8.4 11.9	1.0 1.0	10.0 13.5	1.0 1.0	11.0 14.5	ns
	B to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.9 5.4	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	7.5 9.5	
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or OEB to YB	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.6 9.1	10.6 14.1	1.0 1.0	12.5 16.0	1.0 1.0	13.5 17.0	ns
	OEB to 1B	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		4.7 6.2	7.3 9.3	1.0 1.0	8.5 10.5	1.0 1.0	9.5 11.5	
t _{PLZ} ,	Output Disable Time OEA to YA or OEB to YB	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$		10.3	14.0	1.0	16.0	1.0	17.0	ns
t _{PHZ}		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$		6.7	9.2	1.0	10.5	1.0	11.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.0		1.0		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6						pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 7)	19	pF

NOISE CHARACTERISTICS (MC74VHC244)

		T _A = 25°C		
Symbol	Parameter	Тур Мах		Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}		-0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage	1.5		V

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS (MC74VHCT244A)

		V _{CC}		$T_A = -40$	T _A = - 40 to 85°C		T _A = 85 to 125°C				
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		2.0		V
V _{IL}	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8		0.8	V
V _{OH}	Minimum High-Level	I _{OH} = -50 μA	4.5	4.4	4.5		4.4		4.4		V
	Output Voltage V _{in} = V _{IH} or V _{IL}	I _{OH} = -8 mA	4.5	3.94			3.80		3.66		
V _{OL}	Maximum Low-Level	I _{OL} = 50 μA	4.5		0.0	0.1		0.1		0.1	V
	Output Voltage V _{in} = V _{IH} or V _{IL}	I _{OL} = 8 mA	4.5			0.36		0.44		0.52	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5		2.5	μΑ
Icc	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0		40.0	μΑ
I _{CCT}	Quiescent Supply Current	Per Input: V _{IN} =3.4 V Other Input: V _{CC} or GND	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0			0.5		5.0		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHCT244A)

			T	A = 25°	,C	T _A = - 40	to 85°C	T _A = 85 t	to 125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay A to YA or B to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V } C_L = 15 \text{ pF} $ $C_L = 50 \text{ pF} $		5.4 5.9	7.4 8.4	1.0 1.0	8.5 9.5	11.0 1.0	9.5 10.5	ns
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 15 \text{ pF}$ $C_{L} = 50 \text{ pF}$		7.7 8.2	10.4 11.4	1.0 1.0	12.0 13.0	1.0 1.0	13.5 14.5	ns
t _{PLZ} , t _{PHZ}	Output Disable Time OEA to YA or OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V C}_{L} = 50 \text{ pF}$		8.8	11.4	1.0	13.0	1.0	14.5	ns
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 5.0 ± 0.5 V C _L = 50 pF (Note 8)			1.0		1.0		1.0	ns

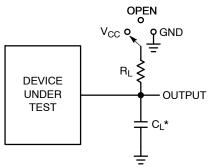
AC ELECTRICAL CHARACTERISTICS (MC74VHCT244A)

		Typical @ 25°C, V _{CC} = 5.0 V			
Symbol	Parameter Min Typ				Unit
C _{PD}	Power Dissipation Capacitance (Note 9)	18			pF
C _{in}	Maximum Input Capacitance		4	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)		9		pF

NOISE CHARACTERISTICS (MC74VHCT244A)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.1	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.9	-1.1	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

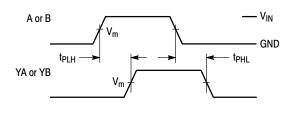
Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position	C _L	R_L
t _{PLH} / t _{PHL}	Open	See AC Characteristics	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	Table	
t _{PHZ} / t _{PZH}	GND		
•	5		-

Figure 2. Test Circuits

SWITCHING WAVEFORMS



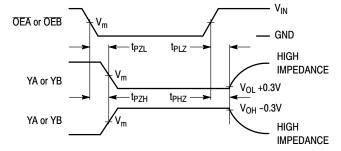


Figure 3. Switching Waveform

Figure 4. Switching Waveform

Device	V _{IN} , V	V _m , V
MC74VHC244	V _{CC}	50% x V _{CC}
MC74VHCT244A	3 V	1.5 V

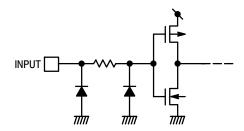


Figure 5. Input Equivalent Circuit

 $^{^{\}star}C_L$ Includes probe and jig capacitance Input signal $t_R=t_F=3\,\,\text{ns}$

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74VHC244DWR2G	VHC244G	SOIC-20 WB	1000 / Tape & Reel
MC74VHC244DTG	VHC 244	TSSOP-20	75 Units / Rail
MC74VHC244DTR2G	VHC 244	TSSOP-20	2500 / Tape & Reel
MC74VHC244DTR2G-Q*	VHC 244	TSSOP-20	2500 / Tape & Reel
MC74VHCT244ADWR2G	VHCT244AG	SOIC-20 WB	1000 / Tape & Reel
MC74VHCT244ADTG	VHCT 244A	TSSOP-20	75 Units / Rail
MC74VHCT244ADTR2G	VHCT 244A	TSSOP-20	2500 / Tape & Reel
MC74VHCT244ADTR2G-Q*	VHCT 244A	TSSOP-20	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

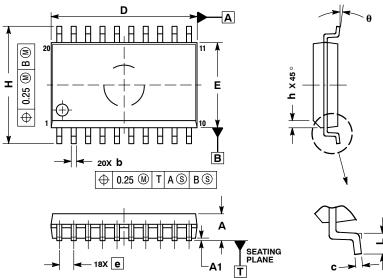




SOIC-20 WB CASE 751D-05 **ISSUE H**

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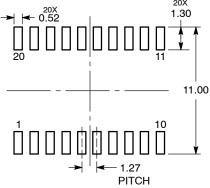




- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

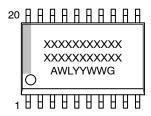
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27 BSC			
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1	

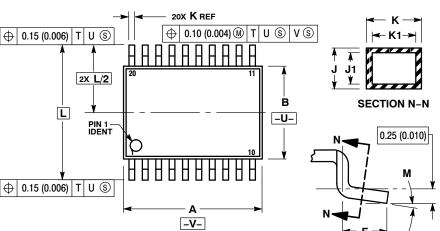
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

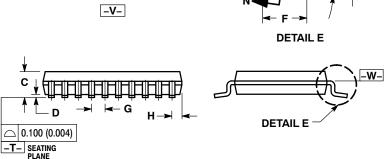


TSSOP-20 WB CASE 948E ISSUE D

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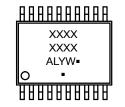
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	٥°	gο	٥°	gο

GENERIC SOLDERING FOOTPRINT MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1	

DIMENSIONS: MILLIMETERS

0.65

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0.36

16X

1.26

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